Electric-field induced tuning of electronic correlation in weakly confining quantum dots

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(Dated: June 8, 2021)

We conduct a combined experimental and theoretical study of the quantum confined Stark effect in GaAs/AlGaAs quantum dots obtained with the local droplet etching method. In the experiment, we probe the permanent electric dipole and polarizability of neutral and positively charged excitons weakly confined in GaAs quantum dots. We interpret those results with the help of calculations based on the full-configuration-interaction method which show excellent quantitative agreement with the micro-photoluminescence (µ-PL) measurements and allow us to elucidate the role of Coulomb interactions among the confined particles and – even more importantly – of electronic correlation effects on the Stark shifts. Moreover, we show how the electric field alters properties such as built-in dipole, binding energy, and heavy-light hole mixing of multiparticle complexes in weakly confining systems, underlining the deficiencies of commonly used models for the quantum confined Stark effect.

Semiconductor quantum dots (QDs) are one of the most promising quantum light source in quantum technology, as they combine excellent optical properties with the compatibility to semiconductor processing and the potential for scalability. 1-11 Meanwhile, they provide also a platform for photon-to-spin conversion 10,11, building up bridges between photonic and spin qubits 12,14. In the process of spin initialization and manipulation 15, the applied electric field (F_d) among others modifies the energy and spatial distribution of the confined single-particle (SP) states via the so-called quantum confined Stark effect (QCSE), leading to deep changes in the electronic and optical properties of QDs 16-19. Therefore, for the possible usage in quantum networks, a fundamental understanding of the effects of F_d in that kind of quasi-zero dimensional structures is highly desirable.

Here we choose GaAs/AlGaAs QDs fabricated by the local droplet etching (LDE) method 20-25 via molecular beam epitaxy (MBE) as our investigation subject. Superior to other QDs formed by conventional strain or droplet epitaxy, LDE GaAs QD has negligible strain and minimized intermixing of core and barrier material 20-22,25, thus, are particularly clean and favorable platform both for fundamental investigations and application of QCSE. Meanwhile, because of their state-of-the-art photon indistinguishabilities 27 and near-unity entanglement fidelities of 0.978(5) 28, devices based on LDE GaAs QDs have recently succeeded in the demonstration of entanglement swapping 29,30 and the quantum key distribution. 31,32

To the best of our knowledge, only a few works have been dealing with the physics of GaAs QDs in externally applied electric fields. 15,33-38 As an example, in Refs. 37-38 F_d’s applied perpendicular to the growth plane were used to modify the Fine structure splitting (FSS) of neutral excitons (X^0) confined in natural GaAs QDs (thickness or alloy fluctuations in thin quantum wells, with poorly defined density, shape, and optical properties). Besides that, simplified simulation models based on the SP assumption were built up to explain the effect of charge noise caused by trapping/detrapping occurring at random places in the host material around QD, 39 but neither fully explain the behavior of the charge carriers, nor take into account correlation effects 33 completely. On the contrary, we note that correlation is of particular importance in the GaAs/AlGaAs QD system because of the generally large size of the studied dots. 40-42 For example, excluding the correlation effects, the binding energy (E_b) of positively charged exciton (X^+) with respect to X^0 shall be rather small and attain negative (anti-binding state) rather than positive (binding state) values, 43 contrasting with the experimental observations. 44,46 Positive E_b have been theoretically calculated for GaAs QDs obtained by “hierarchical self-assembly”, 41 yet still not quantitatively agreeing with experiment. In addition, detailed studies of the electric field effects on the Coulomb interactions between electrons (e^-) and holes (h^+) in GaAs QDs are still lacking.
In this work, we conduct a combined experimental and theoretical study of the QCSE in individual GaAs QDs. Our experiments, based on micro-photoluminescence (µ-PL) spectroscopy, offer direct information on the permanent electric dipole moment (p) and polarizability (β) of relevant energy states in GaAs QDs, which sensitively depend on carrier interactions in those nanostructures. Furthermore, we perform calculations of the aforementioned complexes using the configuration-interaction (CI) method \cite{47,50} with SP basis states obtained using the eight-band k·p method computed with the inclusion of the full elastic strain tensor and piezoelectricity (up to second order \cite{51,53}) by Nextnano \cite{54} software package.

We start by measuring the Stark shifts of X\(^0\) and X\(^+\) states of GaAs QDs by µ-PL spectroscopy. The shape of the QD is defined by the Al-droplet-etched nanohole (NH) (see Fig. 1 (a)), with depth of \(\sim 7\) nm, full width at half maximum depth of \(\sim 33\) nm) and \(\sim 1 - 2\) nm thick “wetting layer” (WL) above the Nhs formed by the GaAs filling. \cite{25,62} In order to apply \(F_d\) along the growth direction, the QDs were embedded in the intrinsic region of a p-i-n diode structure. \cite{55}

Figure 1 (b) shows typical PL spectra obtained from a QD (marked as QD1) as a function of \(F_d\). Near \(F_d = 0\), an isolated X\(^0\) transition is found at \(1.611407(2)\) eV, accompanied by multie exciton states at lower energies (1.60843 – 1.60381 eV). This configuration qualitatively agrees with other reports on GaAs QDs grown by LDE, \cite{15} droplet epitaxy, \cite{57} and hierarchical self-assembly, \cite{40,41} and is different from that observed in In(Ga)As QDs, for which X\(^+\) usually attains higher energy compared to X\(^0\). \cite{18,58,59} Energy shifts for \(F_d \lesssim 30\) kV/cm are not observed in our experiments because of the current injection in the diode. Investigations on the electroluminescence (EL) of this type of device have been reported previously in Ref. \cite{60}. For \(F_d \gtrsim 240\) kV/cm the \(\mu-\)PL signal is faint and cannot be tracked because of the field ionization of excitons. \cite{59} Overall, the emission energy is red-shifted by almost 24 meV upon increasing \(F_d\). We extract the energy of X\(^0\) and X\(^+\) by performing Gaussian fitting of \(\mu-\)PL spectra and for the corresponding \(F_d\) of five QDs and plot those in Fig. 1 (d).

In the simulation we have modeled the NH as a cone with the basal diameter of 40 nm, height of 4 – 9.5 nm and WL thickness of 2 nm. Note, that in order to show that our theory results are more general, we also compute lens-shape dots with same basal diameter and heights as for the reference cone-shaped dots. The simulated Stark shifts of the QDs are plotted together with the experimental data from five dots in the Fig. 1 (d). Calculation results are also shown for \(F_d < 0\), which is however not experimentally accessible with the present diode structure. Interestingly, the parabolic shifts are not symmetric around \(F_d = 0\), as already predicted in Ref. \cite{33}. Concomitantly, the maximum of the emission energy appears at \(F_d > 0\). Both effects are the result of the asymmetric shape of QDs along the \(F_d\) direction, i.e., z-axis combined with the different behaviors of \(e^-\) and \(h^+\) as their wave-functions move along z-axis, thus, experiencing different lateral confinements. On the other hand, the maximum of emission energy at non-zero \(F_d\) can be interpreted with the existence of a permanent electric dipole, which we will discuss in the following.

The shifts of the X\(^0\) and X\(^+\) induced by \(F_d\) are commonly described by the quadratic equation

\[
E(F_d) = E_0 + p_z F_d + \beta F_d^2, 
\]

where \(E_0\) is the emission energy for \(F_d = 0\), and \(p_z\) and \(\beta\) can be intuitively interpreted as the permanent electric dipole moment and polarizability of the corresponding complexes, respectively. \cite{18,58,59,61,62} The quantity \(p_z/e\) can be seen as the distance between \(e^-\) and \(h^+\) probability densities along the z-axis, see also Fig. 1 (c). Figure 2 (a) summarizes the fitted values of \(p_z/e\) for X\(^0\) and X\(^+\) for five QDs. \cite{61} The negative \(p_z/e\) values are close to the experimental data reported in Ref. \cite{65} (\(p_z/e = -0.39\) and \(-0.31\) nm for QD1 and QD2).

In order to deduce \(p_z/e\) also from our theory data, we first tested the same method as for experiment, i.e., fit-
We show the \( p_z / e \) component of Eq. 2 in Fig. 2 (a) for \( X^0 \) and \( X^+ \). The calculations indicate that \( p_z / e \) of excitons confined in GaAs QDs is very small. This is very different from the situation typically encountered in strained QDs, where the dipole is mostly determined by opposite effects, the alloy gradient and the strain inhomogeneities combined with piezoelectricity. 19, 61, 67–73 Since we find that \( p_z / e \) is in atomic scale in both experiment and theory it is reasonable to discard \( p_z / e \) term in fitting using Eq. 1 in case of our data. 63

In contrast to \( p_z / e \), we find for \( \beta / e \) of \( X^0 \) (\( X^+ \)) a more consistent agreement of fits by Eq. 1 between theory and experiment, see Fig. 2 (b). 66 Moreover, \( \beta / e \) shows a clear dependence on \( E_b \). The larger QDs, with smaller \( E_b \), tend to have larger magnitude of \( \beta_{X^0} (\beta_{X^+}) \) for \( X^0 \) (\( X^+ \)), consistent with the results reported in Ref. 63. The theoretical prediction in Refs. 59 and 63 also pointed out that with a fixed shape and chemical composition profile, \( \beta \) is mostly sensitive to the QD height. The taller QD provides in fact more room along z-direction for the confined \( e^- h^+ \) pairs to move away from each other when pulled apart by \( F_d \), resulting in a stronger red-shift in spite of the reduced \( e^- h^+ \) binding energy.

To describe the evolution of the relative binding energy \( E_b = E(X^0) - E(X^+) \) with \( F_d \) we assume a quadratic dependence as in Eq. 1 with omitted linear term (see above discussion)

\[
E_b(F_d) = E_{b,0} + \beta_{E_b} F_d^2,
\]

where \( E_{b,0} \) marks \( E_b \) for \( F_d = 0 \). Thereafter, using Eq. 3 we fit the difference between \( E(X^0) \) and \( E(X^+) \) taken from corresponding dependencies in Fig. 1 (d) and we obtain the parameters \( E_{b,0} \) and \( \beta_{E_b} \), which we show alongside the calculated values in Fig. 2 (c) and (d), respectively.

From Fig. 2 (c) we see that the calculated \( E_{b,0} \) is satisfyingly close to the experimental data for both the cone-
and the lens-shaped dots, in contrast to former CI calculations. To the best of our knowledge, this is the first time that a positive trion binding energy as large as 5 meV is obtained from realistic calculations. The $E_{b,0}$ values are also close to those reported in Ref. [14] ($= E_{b,0}$ linearly increasing from $\sim 2.4$ to $\sim 2.9$ meV for emission energies increasing from $\sim 1.56$ to $\sim 1.61$ eV). We ascribe the agreement between our theory and experiment to an almost full inclusion of the correlation effects, which will be also discussed and tested in the following.

However, first let us show that the physical reason for the disagreement of Eq. (1) with theory is due to the omission of the effect of correlation as well. We start by writing the energies of the final photon states after recombination of $X^0$ and $X^+$ as \[ E(X^0) = \varepsilon_e - \varepsilon_h - J_{eh,X^0} - \delta(X^0) \] and \[ E(X^+) = \varepsilon_e - \varepsilon_h - 2J_{eh,X^+} + J_{hh} - \delta(X^+), \] respectively. Here, $\delta(X^0)$ is the energy of $X^+$ before recombination, $J_{eh,X^0}, J_{eh,X^+}, J_{hh}$ the Coulomb interactions of $e^-h^+$ pairs in $X^0$ and $X^+$, and that for $h^+-h^+$ pair, respectively; $\varepsilon_e$ ($\varepsilon_h$) is the SP $e^-$ ($h^+$) energy, $\delta(X^0)$ ($\delta(X^+)$) marks the energy change due to the effect of correlation for $X^0$ ($X^+$). Consequently, the $E_b$ can be written as

\[ E_b = 2J_{eh,X^+} - J_{eh,X^0} - J_{hh} - \delta \]

where $\delta = \delta(X^0) - \delta(X^+)$. Note that we have completely neglected the exchange interaction since we found that to be $\approx 100$ times smaller than direct Coulomb interaction in our CI calculations. In Fig. 2 (f) we plot $E_0$-dependence of $\beta_{eh}/e$ for $J_{eh}, J_{eh} - J_{hh}, J_{hh},$ and $E_{b,sim}$ from simulation. Note, that $\beta_{eh}/e$ values were obtained by fit using Eq. 4 of the theory dependencies of $J_{eh}, J_{eh} - J_{hh}, J_{hh},$ and $E_{b,sim}$ on $F_d$ computed by CI with 12×12 SP basis. Clearly, we find that $J_{hh}$ for $J_{hh}$ is more pronounced compared to that in flatter QDs. The reason is that taller QDs facilitate the $e^- - h^+$ separation (polarization) under the influence of vertical $F_d$. On the other hand, $|\beta_{eh}|$ for $J_{hh}$ is smaller in larger QDs. The reason is that larger QDs allow the separation between $h^+$ to be larger, thus reducing the Coulomb repulsion. Since the value of $|\beta_{eh}|$ for $J_{hh}$ is smaller than that of $J_{eh}$ for every QD, $J_{hh}$ for $E_{b,sim}$ has larger contribution of that corresponding to $J_{eh}$. However, we notice that $|\beta_{eh}|$ for $J_{hh}$ is still smaller than that of $E_{b,sim}$ (see the corresponding curves in Fig. 2 (f)). That means, besides $J_{eh}$ and $J_{hh}$ there must be another important variable in Eq. 4 changing with $F_d$, therefore, the correlation effect $\delta$ must also vary with $F_d$.

To prove the importance of the correlation effect in our system, we calculated $E_b$ based on the CI model for the simulation with increasing SP basis from two $e^-$ and two $h^+$ ($2 \times 2$) states to twenty-four $e^-$ and twenty-four $h^+$ ($24 \times 24$) states. The result is plotted in Fig 2 (e). Clearly, in the absence of correlation, i.e., using $2 \times 2$ and $4 \times 4$ basis, $X^+$ is anti-binding with respect to $X^0$, in contradiction with the experiments. However, with increasing basis size, the effect of correlation gains importance and $X^+$ becomes binding with respect to $X^0$. The increase of $E_b$ is steep up to $12 \times 12$ basis, where it almost saturates. Note, that the dependence was computed for the largest considered QD, i.e., $h = 9.5$ nm, where the effect of correlation was expected to be the most significant.

We discuss now to the effect of $F_d$ on heavy $(|HH\rangle)$, light $(|LH\rangle)$, and spin-orbit $(|SO\rangle)$ hole Bloch state mixing for $X^0$ and $X^+$ ground states. The corresponding normalized contents of those components, i.e., $|\rho_{HH}(X^0) + \rho_{LH}(X^0) + \rho_{SO}(X^0)|$ in Fig. 2 (f) versus electric field $F_d$. The colors identify the heights of QDs in the same fashion as in Fig. 2 where blue corresponds to $h = 4$ nm and red to $h = 9.5$ nm. The Bloch state contents for both $X^0$ and $X^+$ were calculated using the CI model with the basis consisting of 12 SP $e^-$ and 12 SP $h^+$ state, with the effects of the direct and the exchange Coulomb interaction, and the correlation effect being included.

![FIG. 3. Contribution of $|HH\rangle$, $|LH\rangle$ and $|SO\rangle$ states normalized to total sum of contributions of these components, i.e., $|\rho_{HH}(X^0) + \rho_{LH}(X^0) + \rho_{SO}(X^0)|$, in $X^0$ (top row) and $X^+$ (bottom row) versus electric field $F_d$. The colors identify the heights of QDs in the same fashion as in Fig. 2 where blue corresponds to $h = 4$ nm and red to $h = 9.5$ nm.](image)
The configuration interaction calculation clearly show the charge carriers in GaAs QD. The experimental data and of the electric field on the Coulomb interaction among calculations of multiparticle states, we reveal the influence Bloch states, hence, the larger contribution of $|\phi_y\rangle$ content of generally delocalizes, leading to the faster increase of the hole wavefunction leaks into the wetting layer and laterally delocalizes, leading to the faster increase of the content of $|\text{HH}\rangle$ states. We assume that for the same $F_d$ ($F_d > 50$ kV/cm for $X^0$) all wavefunctions leak into the wetting layer with the same amount of probability density. Hence, the wavefunctions, with larger volume, i.e., for bigger QDs, consist of more $|p_z\rangle$ and $|p_y\rangle$ Bloch states, hence, the larger contribution of $|\text{HH}\rangle$.

In summary, by conducting detailed $\mu$-PL spectroscopy measurements of the emission from LDE-grown GaAs/AlGaAs QDs modulated by an externally applied electric field and in conjunction with conscientious calculations of multiparticle states, we reveal the influence of the electric field on the Coulomb interaction among charge carriers in GaAs QD. The experimental data and the configuration interaction calculation clearly show the dot size dependence of the polarizability of $X^0$ and $X^+$. Thorough analysis of configuration interaction calculations sheds light on the deficiencies of the commonly used analysis of the quantum confined Stark effect by highlighting the striking effect of correlation and the direct Coulomb interaction energy between holes, which change with applied field and which are also significantly influenced by the asymmetry of QD along the field direction, especially in large quantum dots. Moreover, we analysed the Bloch state composition of exciton and trion complexes as a function of applied electric field and emphasize the influence of QD height as well. Finally, we note that our multiparticle simulation model based on the full configuration interaction approach with large number of single-particle basis states provides excellent quantitative agreement with the experiment, and proves the non-negligible role of correlation effect on Stark shift for the nanosystems.

The authors thank A. Haliovic, U. Kainz, J. Martín-Sánchez, T. Lettner for helpful discussions on the device fabrication. This project has received funding from the Austrian Science Fund (FWF): FG 5, P 29603, P 30459, I 4380, I 4320, and I 3762, the Linz Institute of Technology (LIT) and the LIT Secure and Correct Systems Lab funded by the state of Upper Austria and the European Union’s Horizon 2020 research and innovation program under Grant Agreement Nos. 899814 (Qurope), 654384 (ASCENT+), YH Huo is supported by NSFC (Grant No. 11774326), National Key R&D Program of China (Grant No. 2017YFA0304301) and Shanghai Municipal Science and Technology Major Project (Grant No.2019SHZDZX01). R. Trotta is supported by the European Research council (ERC) under the European Union’s Horizon 2020 Research and Innovation Programme (SPIRIT) under Grant Agreement No. 679183. D.C. and P.K. were financed by the project CUSPIDOR (Grant No.2019SHZDZX01). R. Trotta is supported by the European Research council (ERC) under the European Union’s Horizon 2020 Research and Innovation Programme (SPIRIT) under Grant Agreement No. 679183. This project has received funding from the Ministry of Education, Youth and Sports of the Czech Republic and funding from European Union’s Horizon 2020 (2014-2020) research and innovation framework programme under grant agreement No 731473. This project 17FUN06 SIQUST has received funding from the EMPIR programme co-financed by the Participating States and from the European Union’s Horizon 2020 research and innovation programme.


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See Supplemental Material at [URL will be inserted by publisher] for section SIII. giving the values of the fitted $p_z/e$ and $\beta$ of five studied dots. ()


See Supplemental Material at [URL will be inserted by publisher] for section SV. for the dependencies of the computed direct Coulomb integrals on $F_d$ and the corresponding fits. ()

See Supplemental Material at [URL will be inserted by publisher] for section SVI. for the equations giving the conversion between $\{|S\rangle, |HH\rangle, |LH\rangle, |SO\rangle\} \otimes \{|\uparrow\rangle, |\downarrow\rangle\}$ Bloch states and $\{|s\rangle, |px\rangle, |py\rangle, |pz\rangle\} \otimes \{|\uparrow\rangle, |\downarrow\rangle\}$ Bloch states. ()